

## Features

- GaN on SiC Depletion-Mode Transistor Technology
- Internally Matched
- Common-Source Configuration
- Broadband Class AB Operation
- RoHS\* Compliant and 260°C Reflow Compatible
- +50 V Typical Operation
- MTTF = 600 Years ( $T_J < 200\text{ }^{\circ}\text{C}$ )

## Applications

- L-Band pulsed radar.

## Description

The MAGX-001214-650L0x is a gold-metalized matched Gallium Nitride (GaN) on Silicon Carbide (SiC) RF power transistor optimized for pulsed L-Band radar applications. Using state of the art wafer fabrication processes, these high performance transistors provide high gain, efficiency, bandwidth, and ruggedness over a wide bandwidth for today's demanding application needs. High breakdown voltages allow for reliable and stable operation under more extreme mismatch load conditions compared with older semiconductor technologies.

## MAGX-001214-650L00



## Ordering Information

Part Number	Description
MAGX-001214-650L00	GaN Transistor
MAGX-L21214-650L00	1200-1400 MHz Evaluation Board

## Typical RF Performance Under Standard Operating Conditions, $P_{OUT} = 650\text{ W}$ (Peak)

Freq. (MHz)	$P_{IN}$ (W)	Gain (dB)	$I_D$ (A)	Eff. (%)	RL (dB)	Droop (dB)	+1dB OD (W)	VSWR-S (3:1)
1200	8.7	18.8	21.3	61.0	-13.9	0.2	717	S
1250	8.5	18.9	22.0	58.9	-13.8	0.3	726	S
1300	8.0	19.1	22.4	57.8	-13.5	0.3	724	S
1350	7.0	19.7	21.8	59.7	-15.8	0.3	723	S
1400	7.0	19.7	21.1	61.4	-15.0	0.2	697	S

\* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

## GaN on SiC HEMT Pulsed Power Transistor 650 W Peak, 1200-1400 MHz, 300 $\mu$ s Pulse, 10% Duty

Rev. V3

### Electrical Specifications: Freq. = 1200 - 1400 MHz, $T_A = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
<b>RF Functional Tests</b>						
Peak Input Power	$V_{DD} = 50\text{ V}$ , $I_{DQ} = 500\text{ mA}$ Pulse Width = 300 $\mu$ s, Duty Cycle = 10% $P_{OUT} = 650\text{ W Peak (65 W avg.)}$	$P_{IN}$	-	7.5	10.3	W
Power Gain		$G_P$	18	19.5	-	dB
Drain Efficiency		$\eta_D$	55	60	-	%
Pulse Droop		Droop	-	0.3	0.6	dB
Load Mismatch Stability		VSWR-S	-	2:1	-	-
Load Mismatch Tolerance		VSWR-T	-	3:1	-	-

### Electrical Characteristics: $T_A = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
<b>DC Characteristics</b>						
Drain-Source Leakage Current	$V_{GS} = -8\text{ V}$ , $V_{DS} = 175\text{ V}$	$I_{DS}$	-	1.7	33	mA
Gate Threshold Voltage	$V_{DS} = 5\text{ V}$ , $I_D = 90\text{ mA}$	$V_{GS(TH)}$	-5	-2.9	-2	V
Forward Transconductance	$V_{DS} = 5\text{ V}$ , $I_D = 21\text{ mA}$	$G_M$	16.2	21.7	-	S
<b>Dynamic Characteristics</b>						
Input Capacitance	Not applicable - Input matched	$C_{ISS}$	N/A	N/A	N/A	pF
Output Capacitance	$V_{DS} = 50\text{ V}$ , $V_{GS} = -8\text{ V}$ , Freq. = 1 MHz	$C_{OSS}$	-	55	-	pF
Reverse Transfer Capacitance		$C_{RSS}$	-	5.5	-	pF

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### Absolute Maximum Ratings<sup>1,2,3</sup>

Parameter	Limit
Drain Voltage ( $V_{DD}$ )	+65 V
Gate Voltage ( $V_{GG}$ )	-8 to 0 V
Drain Current ( $I_{DD}$ )	27 A
Input Power <sup>4</sup> ( $P_{IN}$ )	$P_{IN}$ (nominal) + 3 dB
Operating Junction Temperature <sup>5</sup>	250°C
Peak Pulsed Power Dissipation at 85°C	700 W
Operating Temperature Range	-40 to +85°C
Storage Temperature Range	-65 to +150°C
ESD Min. - Charged Device Model (CDM)	1300 V
ESD Min. - Human Body Model (HBM)	4000 V

- Exceeding any one or combination of these limits may cause permanent damage to this device.
- MACOM does not recommend sustained operation near these survivability limits.
- For saturated performance it is recommended that the sum of ( $3 * V_{DD} + |V_{GG}|$ ) < 175 V.
- Input Power Limit is +3 dB over nominal drive required to achieve  $P_{OUT} = 650$  W.
- Operating junction temperature is measured with infrared (IR) microscope. Junction temperature directly affects a device's MTTF and should be kept as low as possible to maximize lifetime.
  - MTTF =  $5.3 \times 10^6$  hours ( $T_J < 200^\circ\text{C}$ )
  - MTTF =  $6.8 \times 10^4$  hours ( $T_J < 250^\circ\text{C}$ )

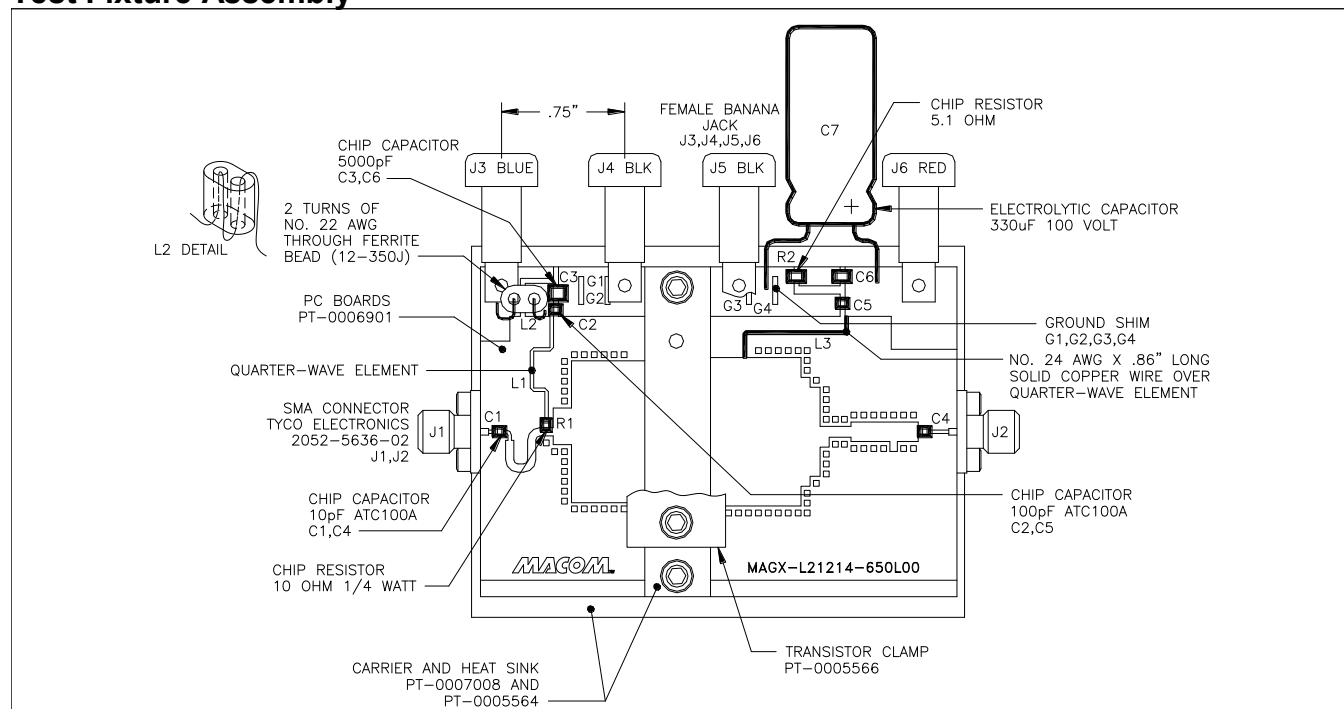
### Thermal Characteristics

Parameter	Test Conditions	Symbol	Typical	Units
Thermal Resistance	$T_C = 70^\circ\text{C}$ , $V_{DD} = 50$ V, $I_{DQ} = 500$ mA, $P_{OUT} = 650$ W Pulse Width = 300 $\mu$ s, Duty Cycle = 10%	$\Theta_{JC}$	0.25	$^\circ\text{C/W}$

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### Test Fixture Assembly



Contact factory for gerber file or additional circuit information.

### Test Fixture Impedances

F (MHz)	$Z_{IF}$ ( $\Omega$ )	$Z_{OF}$ ( $\Omega$ )
1200	$0.8 - j0.9$	$1.4 + j0.2$
1250	$0.8 - j0.7$	$1.4 + j0.2$
1300	$0.7 - j0.6$	$1.4 + j0.1$
1350	$0.7 - j0.4$	$1.2 + j0.1$
1400	$0.7 - j0.2$	$1.1 + j0.2$

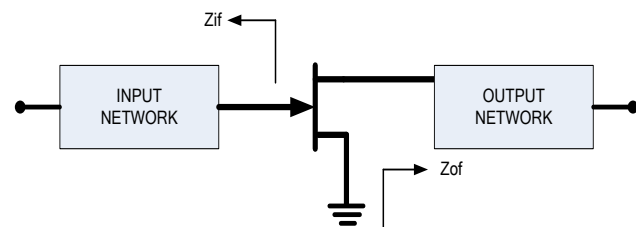
### Correct Device Sequencing

#### Turning the device ON

1. Set  $V_{GS}$  to the pinch-off ( $V_P$ ), typically -5 V.
2. Turn on  $V_{DS}$  to nominal voltage (50 V).
3. Increase  $V_{GS}$  until the  $I_{DS}$  current is reached.
4. Apply RF power to desired level.

#### Turning the device OFF

1. Turn the RF power off.
2. Decrease  $V_{GS}$  down to  $V_P$ .
3. Decrease  $V_{DS}$  down to 0 V.
4. Turn off  $V_{GS}$ .

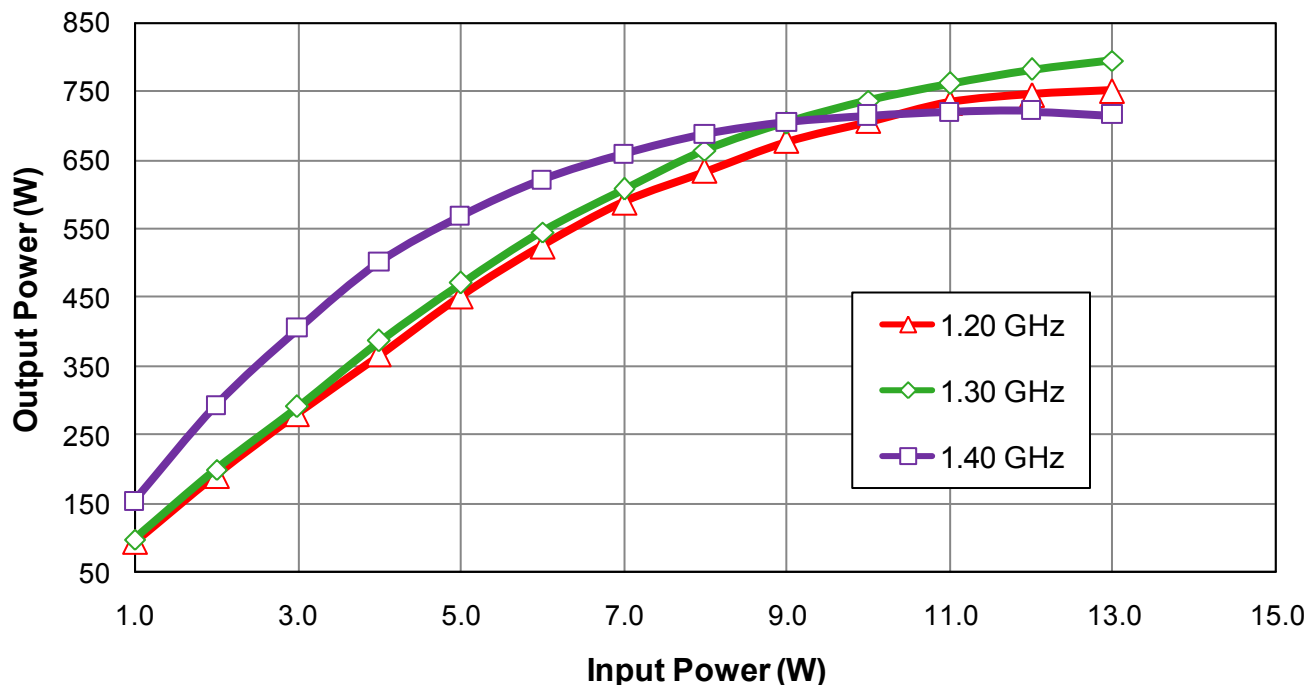


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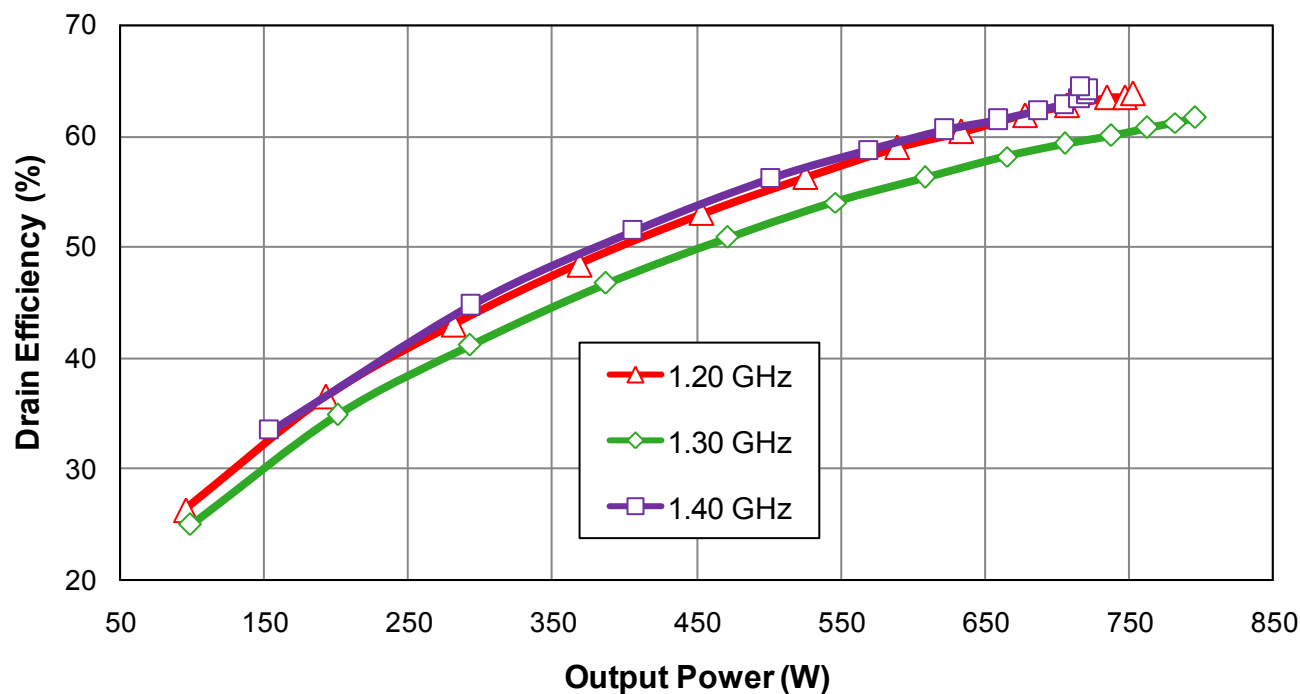
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RF Power Transfer Curve (Output Power vs. Input Power)



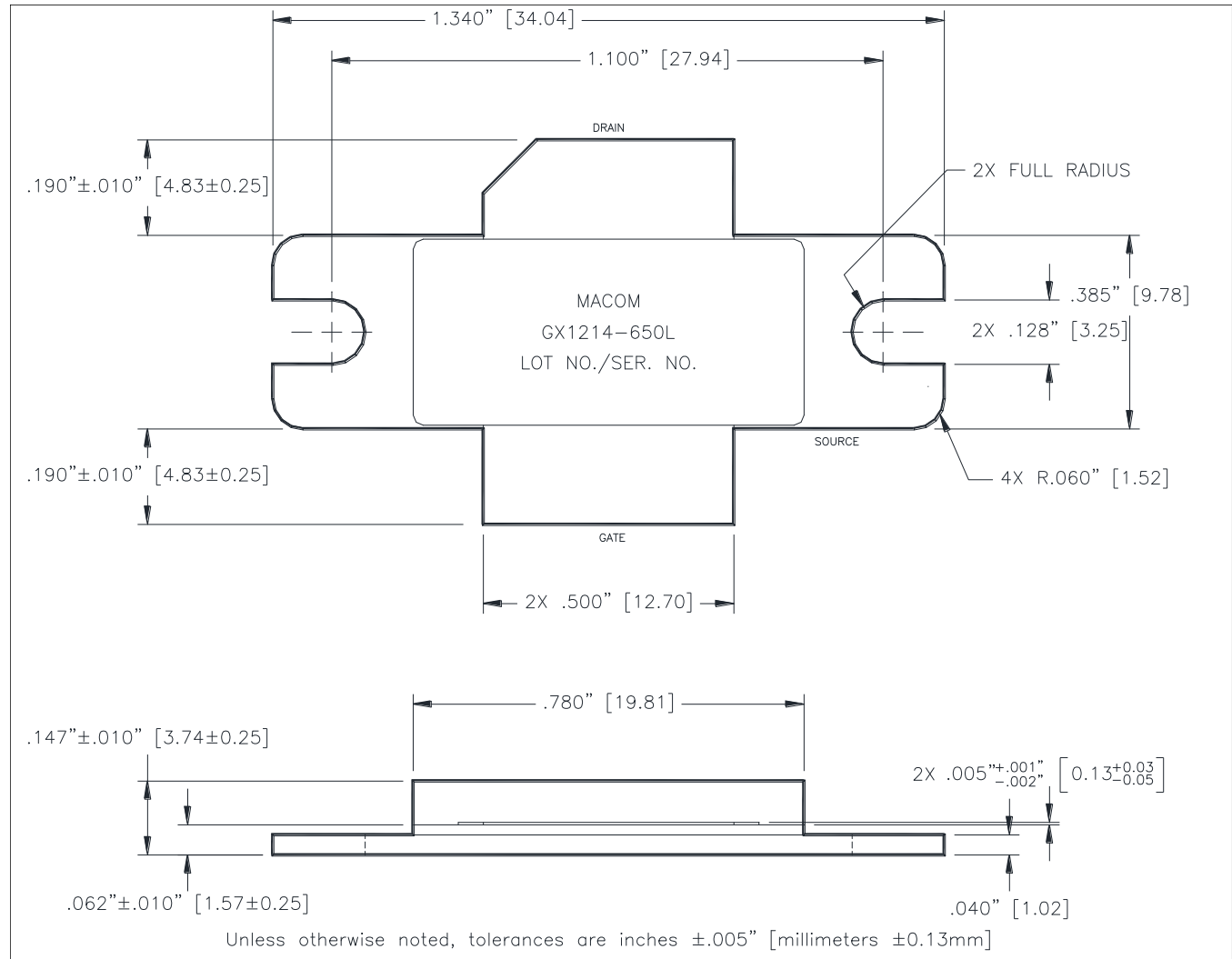
RF Power Transfer Curve (Drain Efficiency vs. Output Power)



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## Outline Drawing MAGX-001214-650L00



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